

# NTR4171P

## Power MOSFET

-30 V, -3.5 A, Single P-Channel, SOT-23

### Features

- Low  $R_{DS(on)}$  at Low Gate Voltage
- Low Threshold Voltage
- High Power and Current Handling Capability
- This is a Pb-Free Device

### Applications

- Load Switch
- Optimized for Battery and Load Management Applications in Portable Equipment like Cell Phones, PDA's, Media Players, etc.

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	-30	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 12$	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	-2.2	A	
		$T_A = 85^\circ\text{C}$	-1.5		
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	-3.5		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	0.48	W
	$t \leq 5$ s		1.25		
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$I_{DM}$	-15.0	A	
Operating Junction and Storage Temperature		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	-1.0	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

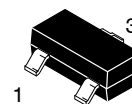
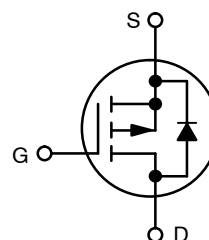
### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	260	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - $t \leq 10$ s (Note 1)	$R_{\theta JA}$	100	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)

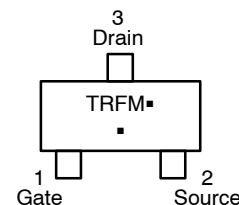
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
-30 V	75 m $\Omega$ @ -10 V	-2.2 A
	110 m $\Omega$ @ -4.5 V	-1.8 A
	150 m $\Omega$ @ -2.5 V	-1.0 A

### P-CHANNEL MOSFET



SOT-23  
CASE 318  
STYLE 21

### MARKING DIAGRAM/ PIN ASSIGNMENT



TRF = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTR4171PT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
NTR4171PT3G	SOT-23 (Pb-Free)	10000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTR4171P

**MOSFET ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250\ \mu\text{A}$ , Reference to $25^\circ\text{C}$		24		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}, T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}, T_J = 85^\circ\text{C}$			-1.0 -5.0	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			$\pm 0.1$	$\mu\text{A}$

**TY CHARACTERISTICS** (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-0.7	-1.15	-1.4	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			3.5		$\text{mV}/^\circ\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -2.2\text{ A}$		50	75	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -1.8\text{ A}$		60	110	
		$V_{GS} = -2.5\text{ V}, I_D = -1.0\text{ A}$		90	150	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5.0\text{ V}, I_D = -2.2\text{ A}$		7.0		S

**CHARGES, CAPACITANCES AND GATE RESISTANCE**

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -15\text{ V}$		720		$\text{pF}$
Output Capacitance	$C_{oss}$			95		
Reverse Transfer Capacitance	$C_{rss}$			65		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V}, I_D = -3.5\text{ A}$		15.6		$\text{nC}$
Threshold Gate Charge	$Q_{G(TH)}$			0.7		
Gate-to-Source Charge	$Q_{GS}$			1.6		
Gate-to-Drain Charge	$Q_{GD}$			2.6		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -3.5\text{ A}$		7.4		$\text{nC}$
Threshold Gate Charge	$Q_{G(TH)}$			0.7		
Gate-to-Source Charge	$Q_{GS}$			1.6		
Gate-to-Drain Charge	$Q_{GD}$			2.6		
Gate Resistance	$R_G$			6.1		$\Omega$

**SWITCHING CHARACTERISTICS,  $V_{GS} = 4.5\text{ V}$**  (Note 4)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V}, I_D = -3.5\text{ A}, R_G = 6\ \Omega$		8.0		ns
Rise Time	$t_r$			11		
Turn-Off Delay Time	$t_{d(off)}$			32		
Fall Time	$t_f$			14		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -3.5\text{ A}, R_G = 6\ \Omega$		9.0		ns
Rise Time	$t_r$			16		
Turn-Off Delay Time	$t_{d(off)}$			25		
Fall Time	$t_f$			22		

**DRAIN-SOURCE DIODE CHARACTERISTICS**

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = -1.0\text{ A}, T_J = 25^\circ\text{C}$		-0.8	-1.2	V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, I_S = -1.0\text{ A}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}$		14		ns
Charge Time	$t_a$			10		
Discharge Time	$t_b$			4.0		
Reverse Recovery Charge	$Q_{RR}$			8.0		

- Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$
- Switching characteristics are independent of operating junction temperatures